

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L2	3	(spin adj coating) same (silicon adj oxide adj glass)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/01/03 11:21
2	BRS	L3	18	(silicon adj oxide adj glass) same (impurity or impurities)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/01/03 11:32
3	BRS	L4	4	plasma adj ion adj implanter	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/01/03 11:34
4	BRS	L5	0	(diffus\$6 or dop\$6) adj10 (impurit\$6) adj3 (ion or ions) adj10 (SOG or (silicon adj oxide adj glass)) adj10 substrate	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/01/03 11:43
5	BRS	L6	190	(barrier adj layer) and (SOG or (silicon adj oxide adj glass)) and (impurit\$6) and (dop\$6)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/01/03 11:47

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BFS	L7	52	6 and shallow	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/01/03 12:57
7	IS&R	L8	242	(438/298).CCLS.	USPAT	2003/01/03 13:54
8	IS&R	L9	297	(438/299).CCLS.	USPAT	2003/01/03 14:50
9	BFS	L11	1455	shallow adj junctions	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/01/03 14:56
10	BFS	L12	53	11 and ((silicon adj oxide adj glass) or SOG)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/01/03 14:57